



News Release / Presseinformation

Infineon Extends 3rd Generation Reverse Conducting IGBT Portfolio, Delivering Industry's Best-in-Class Efficiency and Highest Reliability

Neubiberg, Germany – October 17, 2012 – Infineon Technologies expands its portfolio of the 3rd generation Reverse Conducting (RC) Soft Switching IGBT (Insulated Gate Bipolar Transistor) introducing 1200V and 1350V devices in 30A and 40A, thus responding to the growing demand for higher reliability.

Infineon has a strong record in resonant switching IGBT technologies well-suited for induction cooking applications. The 3rd generation of IGBT was optimized for lower switching and conduction losses and provides best-in-class efficiency in 1100V, 1200V and 1350V.

The new generation provides more than 20 percent lower switching losses resulting in a 5K case temperature reduction during application tests in comparison to the 2nd generation RC IGBT from Infineon. Lower switching losses reduce the thermal stress on the device and lead to longer lifetime and higher reliability. High efficiency, excellent thermal performance and EMI behavior, due to soft switching operation, make it the best suited IGBT on the market for induction cooking, solar and other resonant switching applications.

The portfolio extension of 30A and 40A in 1350V addresses the need of designers to have devices with higher breakthrough voltage and current withstand capabilities, which allow for the development of higher power rated designs in single-end topologies, for example up to 3.6kW.

Additionally, the 30A and 40A devices with 1350V breakthrough voltage enable the extension of the safe operating area (SOA) and higher over-current rating during surge conditions, which gives designers enhanced robustness and reliability.

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“Generation 3 addresses the rising demand for application-specific power switches, that provide an optimized price-performance-ratio and fulfill the specific needs of the targeted applications,” says Roland Stele, Marketing Director IGBT Power Discretes at Infineon Technologies. “The new RC IGBT Generation 3 with extended portfolio defines a new trend for higher system efficiency, better reliability and higher power density. Excellent performance goes along with enhanced robustness of the device.”

The comprehensive product portfolio in 15/20/30/40A in 1200V and 1350V allows designers to choose the IGBT with the best-in-class efficiency and optimal features for their specific application. Flexibility of design in combination with the highest performance streamlines the development process and leads to shorter development time.

All 3rd generation Reverse Conducting IGBT are designed to operate with junction temperatures up to 175°C. Saturation voltage $V_{CE(sat)}$ value ranges from 1.80V to 2.10V for a 15A 1200V device and 40A with a 1350V device respectively at $T_j=175^\circ\text{C}$. Low turn-off soft switching losses ensure highly efficient operation – from 0.15mJ with 15A 1200V IGBT to 1.07mJ for a 40A 1350V device at $dv/dt=150.0\text{V}/\mu\text{s}$ and $T_j=175^\circ\text{C}$.

Availability

3rd generation Reverse Conducting IGBT portfolio is available in 15A, 20A, 30A and 40A current class with 1200V and 1350V breakthrough voltages, as well as 1100V in 30A current class. Devices are available immediately in high production volumes. For more information visit www.infineon.com/rch3

About Infineon

[Infineon](http://www.infineon.com) Technologies AG, Neubiberg, Germany, offers semiconductor and system solutions addressing three central challenges to modern society: [energy efficiency](#), [mobility](#), and [security](#). In the 2011 fiscal year (ending September 30), the company reported sales of Euro 4 billion with close to 26,000 employees worldwide. Infineon is listed on the Frankfurt Stock Exchange (ticker symbol: IFX) and in the USA on the over-the-counter market OTCQX International Premier (ticker symbol: IFNNY).

Further information is available at www.infineon.com

This news release is available online at www.infineon.com/press

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